

Appl. No. 09/966,391
Amdt. Dated December 23, 2003
Reply to Office action of September 26, 2003

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 21 – 34 (original)

Claim 35 (new) A method for providing a charge pump circuit for a DRAM comprising the steps of:

coupling first and second pump cascades in parallel to an output node, each pump cascade having a plurality of pump stages coupled in series;
receiving at said output node charge pumped by the first and the second pump cascades to generate a supply voltage thereat that is greater in magnitude than a power supply voltage; and
constructing each pump stage from a FET configured as a diode and a FET configured as a capacitor, the FETs of the first pump stage of each cascade having a first oxide thickness and the FETs of the last pump stage of each cascade having a second oxide thickness, the second oxide thickness being greater than the first oxide thickness.